BYV29X-600

Ultrafast power diode

Rev.01 - 7 November 2017 Product data sheet

1. General description

Ultrafast, epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Low thermal resistance
- Soft recovery characteristic
- Isolated package
- Low forward voltage drop
- High thermal cycling performance

3. Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

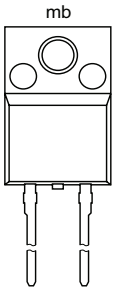
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V_{RRM}	repetitive peak reverse voltage		600				V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_h \leq 85$ °C; Fig. 1; Fig. 2; Fig. 3	9				A
I_{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_h \leq 85$ °C; square-wave pulse	18				A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	91				A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100				A
Symbol	**Parameter**	**Conditions**		**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
V_F	forward voltage	I_F = 8 A; T_j = 25 °C; Fig. 6		-	1.12	1.26	V
		I_F = 8 A; T_j = 125 °C		-	1.03	-	V
		I_F = 8 A; T_j = 150 °C; Fig. 6		-	0.97	1.11	V
Dynamic characteristics							
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C; Fig. 7		-	32	60	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 SOD113 (2-lead TO-220F)	 *001aaa020*
2	A	anode		
mb	mb	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV29X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113

7. Marking

Table 4. Marking codes

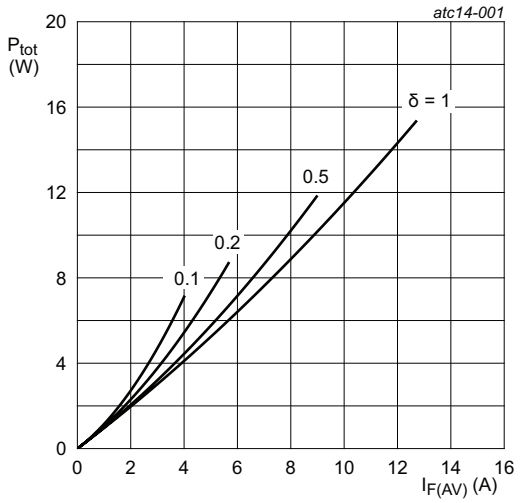
Type number	Marking codes
BYV29X-600	BYV29X-600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

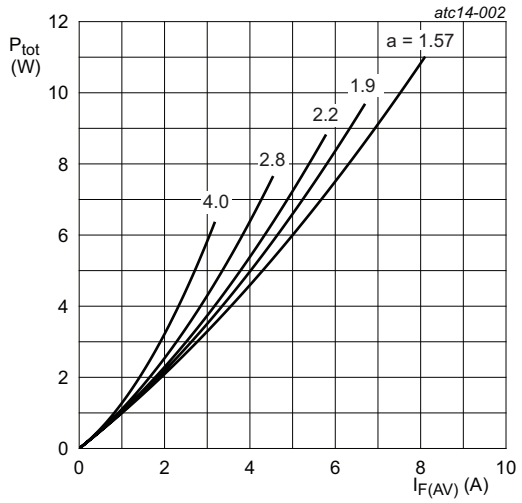
Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_h \leq 85$ °C; Fig. 1; Fig. 2; Fig. 3	9	A
I_{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_h \leq 85$ °C; square-wave pulse	18	A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	91	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100	A
T_{stg}	storage temperature		-40 to 150	°C
T_j	junction temperature		150	°C



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

V_o = 0.943 V; R_s = 0.0208 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)} / I_{F(AV)}$

Vo = 0.943 V; Rs = 0.0208 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

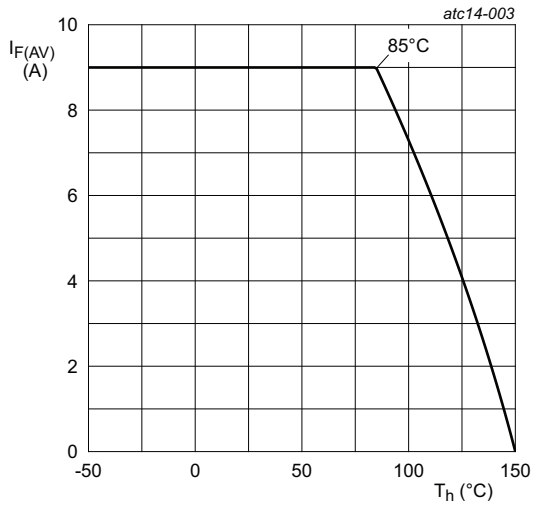


Fig. 3. Forward current as a function of heatsink temperature; maximum values

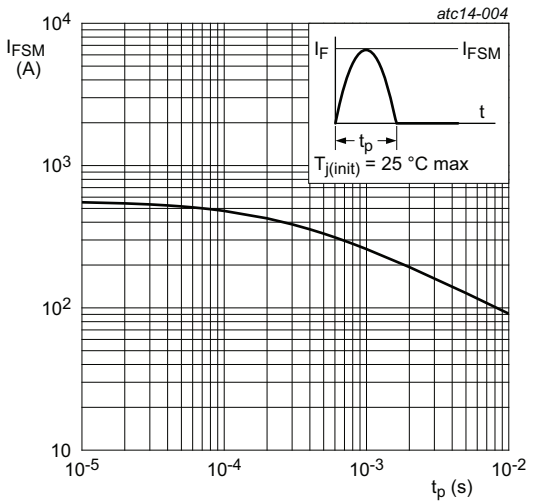


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5		-	-	5.5	K/W
		without heatsink compound		-	-	5.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	55	-	K/W

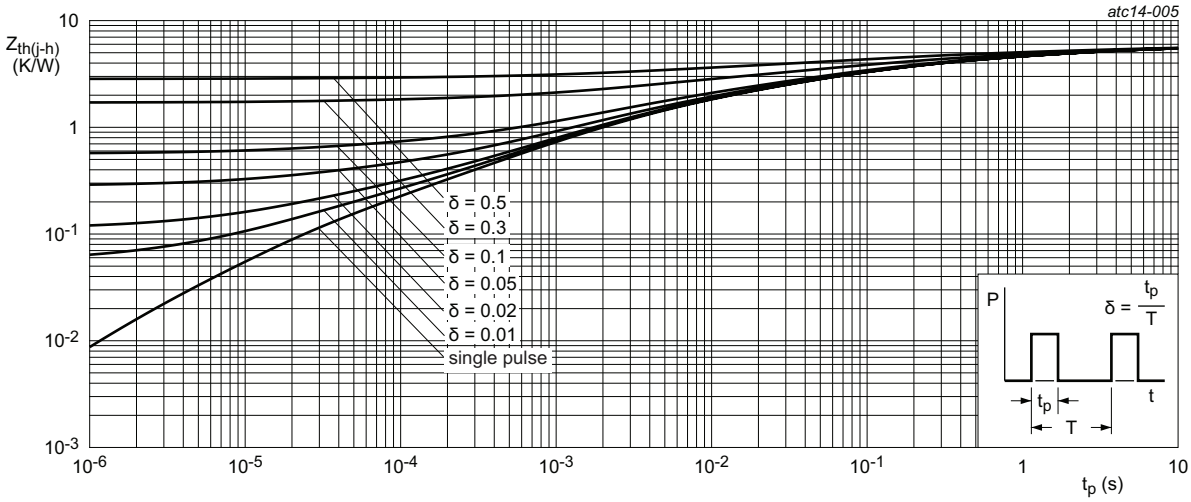


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

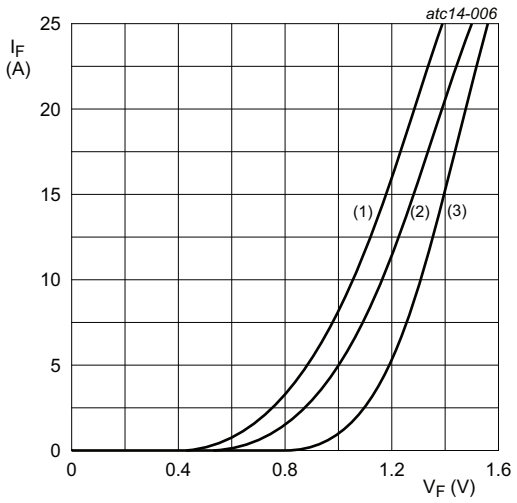
Table 6. Isolation characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C_{isol}	isolation capacitance	from cathode to external heatsink		-	10	-	PF

11. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V_F	forward current	I_F = 8 A; T_j = 25 °C; Fig. 6		-	1.12	1.26	V
		I_F = 8 A; T_j = 125 °C		-	1.03	-	V
		I_F = 8 A; T_j = 150 °C; Fig. 6		-	0.97	1.11	V
I_R	reverse current	V_R = 600 V; T_j = 25 °C		-	2	50	µA
		V_R = 600 V; T_j = 100 °C		-	0.3	-	mA
		V_R = 600 V; T_j = 125 °C		-	-	3	mA
Dynamic characteristics							
Q_r	reverse charge	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C; Fig. 7		-	37	-	nC
t_{rr}	reverse recovery time			-	32	60	ns
I_{RM}	peak reverse recovery current			-	2.3	-	A
dI_{rr}/dt	peak rate of fall of reverse recovery current			-	297	-	A/µs
Q_r	reverse charge	I_F = 8 A; V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 25 °C; Fig. 7		-	220	-	nC
t_{rr}	reverse recovery time			-	43	-	ns
I_{RM}	peak reverse recovery current			-	10	-	A
dI_{rr}/dt	peak rate of fall of reverse recovery current			-	655	-	A/µs
Q_r	reverse charge	I_F = 8 A; V_R = 400 V; dI_F/dt = 200 A/µs; T_j = 25 °C; Fig. 7		-	165	-	nC
t_{rr}	reverse recovery time			-	59	-	ns
I_{RM}	peak reverse recovery current			-	5.6	-	A
dI_{rr}/dt	peak rate of fall of reverse recovery current			-	215	-	A/µs
Q_r	reverse charge	I_F = 8 A; V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 125 °C; Fig. 7		-	425	-	nC
t_{rr}	reverse recovery time			-	57	-	ns
I_{RM}	peak reverse recovery current			-	15	-	A
dI_{rr}/dt	peak rate of fall of reverse recovery current			-	1661	-	A/µs
Q_r	reverse charge	I_F = 8 A; V_R = 400 V; dI_F/dt = 200 A/µs; T_j = 125 °C; Fig. 7		-	315	-	nC
t_{rr}	reverse recovery time			-	70	-	ns
I_{RM}	peak reverse recovery current			-	9	-	A
dI_{rr}/dt	peak rate of fall of reverse recovery current			-	1181	-	A/µs



V_o = 0.943 V; R_s = 0.0208 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

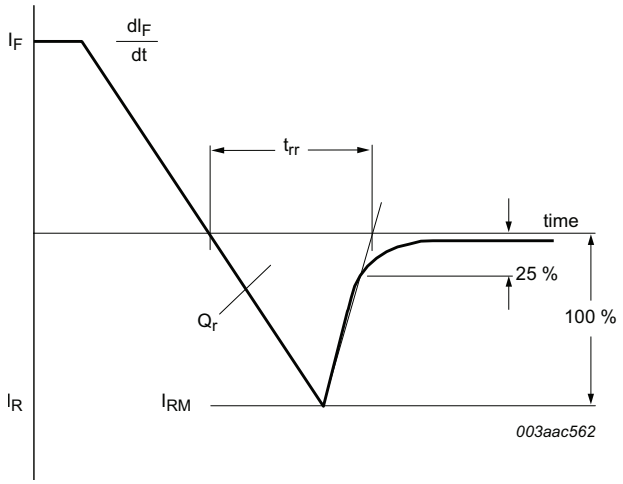
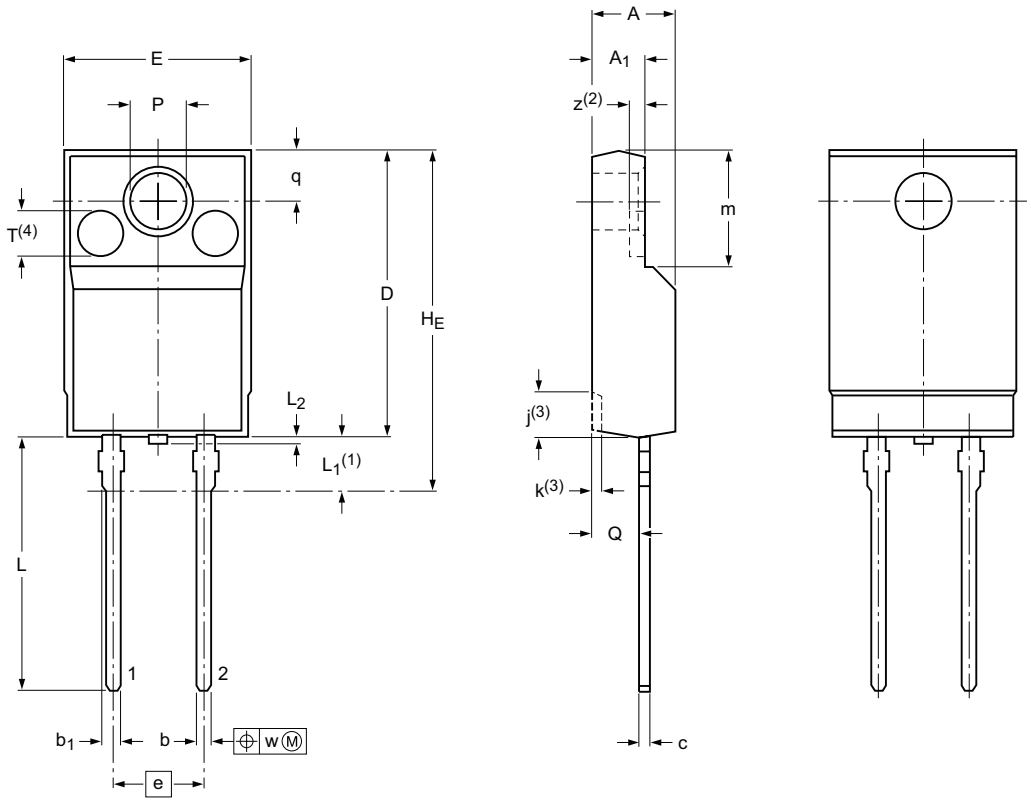


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 `full pack' **SOD113**



Dimensions (mm are the original dimensions)

Unit		A	A_1	b	b_1	c	D	E	e	H_E max	$j^{(3)}$	$k^{(3)}$	L	$L_1{}^{(1)}$	L_2 max	m	P	Q	q	$T^{(4)}$	w	$z^{(2)}$
mm	max	4.6	2.9	0.9	1.1	0.7	15.8	10.3	5.08	19.0	2.7	0.6	14.4	3.3	0.5	6.5	3.2	2.6	2.6	2.55	0.4	0.8
	nom																					
	min	4.0	2.5	0.7	0.9	0.4	15.2	9.7			1.7	0.4	13.5	2.8		6.3	3.0	2.3				

Notes
1. Terminals are uncontrolled within zone L1.
2. z is depth of T.
3. Dot lines area designs may vary.
4. Eject pin mark is for reference only.

sod113_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOD113		2-lead TO-220F				~~07-06-08~~ 15-08-28

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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14. Contents

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